

## Advance Information

# 256KB and 512KB BurstRAM™ Secondary Cache Modules for PowerPC™ PReP/CHRP Platforms

**MPC2104**  
**MPC2105**  
**MPC2106**  
**MPC2107**

The MPC2104/5/6/7 are designed to provide burstable, high performance L2 cache for the PowerPC 60x microprocessor family in conformance with the PowerPC Reference Platform (PReP) and the PowerPC Common Hardware Reference Platform (CHRP) specifications. These products utilize synchronous or asynchronous data RAMs.

The MPC2104, MPC2105, and MPC2106 utilize synchronous BurstRAMs. The modules are configured as 32K x 72, 64K x 72, and 128K x 72 bits in a 182 (91 x 2) pin DIMM format. The MPC2104 uses four of Motorola's 5 V 32K x 18; the MPC2105 uses four of the 5 V 64K x 18; the MPC2106 uses eight of the 5 V 64K x 18. For tag bits, a 5 V cache tag RAM configured as 16K x 12 for tag field plus 16K x 2 for valid and dirty status bits is used.

Bursts can be initiated with the ADS signal. Subsequent burst addresses are generated internal to the BurstRAM by the CNTEN signal.

Write cycles are internally self timed and are initiated by the rising edge of the clock (CLKx) inputs. Eight write enables are provided for byte write control.

The MPC2107 utilizes asynchronous data RAMs. The module is configured as 32K x 64 in the same 182 pin DIMM format. Again, 5 V cache tag RAMs configured as 16K x 12 for tag field plus 16K x 2 for valid and dirty status bits are used. Burst capability is provided in that two burst addresses bypass the address latch.

Presence detect pins are available for auto configuration of the cache control. A serial EEPROM is optional to provide more in-depth description of the cache module. This EEPROM will be available on future revisions of the module family.

The module family pinout will support 5 V and 3.3 V components for a clear path to lower voltage and power savings. Both power supplies must be connected.

All of these cache modules are plug and pin compatible with each other.

- PowerPC-style Burst Counter on Chip (MPC2104/5/6)
- Flow-Through Data I/O (MPC2104/5/6)
- Plug and Pin Compatibility of entire Module Family
- Multiple Clock Pins for Reduced Loading
- All Cache Data and Tag I/Os are LVTTTL (3.3 V) Compatible (MPC2104/5/6)
- Three State Outputs
- Byte Write Capability
- Fast Module Clock Rates: Up to 66 MHz
- Fast SRAM Access Times: 10 ns for Tag RAM Match  
9 ns for Data RAM (MPC2104/5/6)  
15 ns for Data RAM (MPC2107)
- Decoupling Capacitors for Each Fast Static RAM
- High Quality Multi-Layer FR4 PWB With Separate Power and Ground Planes
- 182 Pin Card Edge Module
- Burndy Connector, Part Number: ELF182JSC-3Z50

BurstRAM is a trademark of Motorola.

PowerPC is a trademark of International Business Machines Corp.

This document contains information on a new product. Specifications and information herein are subject to change without notice.

11/8/95



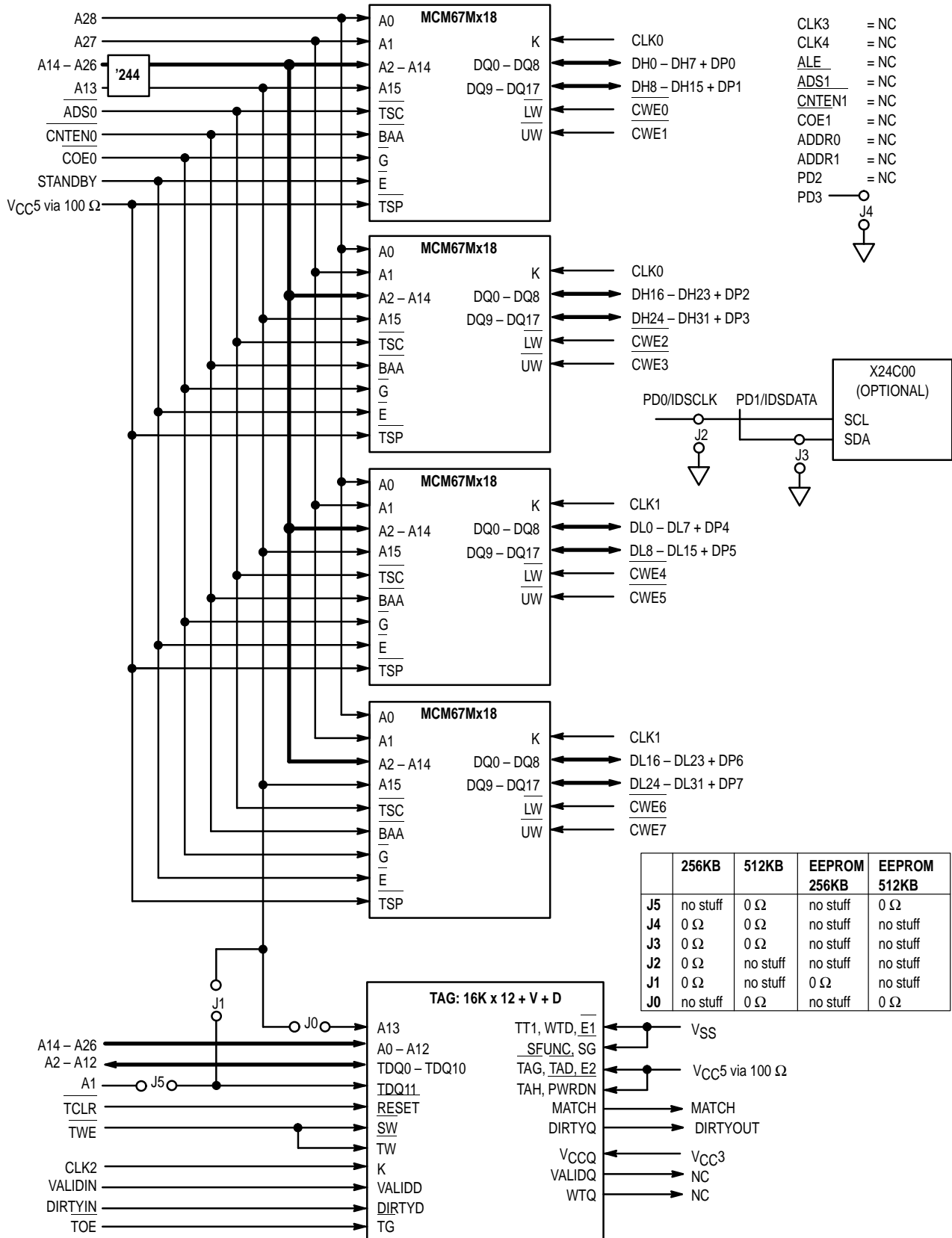
**PIN ASSIGNMENT  
182-LEAD DIMM  
TOP VIEW – CASE TBD**

VSS	92	1	VSS
PD1/DSDATA	93	2	PD0/DSCLK
PD3	94	3	PD2
DH31	95	4	DH30
DH29	96	5	DH28
DH27	97	6	DH26
DH25	98	7	DH24
VCC3	99	8	VCC3
CWE3	100	9	DP3
DH23	101	10	DH22
DH21	102	11	DH20
DH18	103	12	DH19
VSS	104	13	VSS
DH16	105	14	DH17
CWE2	106	15	DP2
DH14	107	16	DH15
DH13	108	17	DH12
VCC5	109	18	VCC5
DH10	110	19	DH11
DH8	111	20	DH9
CWE1	112	21	DP1
DH6	113	22	DH7
VCC3	114	23	VCC3
DH4	115	24	DH5
VSS	116	25	DH3
CLK0	117	26	DH2
VSS	118	27	DH0
DH1	119	28	DP0
CWE0	120	29	VSS
DL31	121	30	CLK1
DL30	122	31	VSS
VSS	123	32	DL28
DL29	124	33	DL26
DL27	125	34	DL24
DL25	126	35	DP7
VCC5	127	36	VCC5
CWE7	128	37	DL22
DL23	129	38	DL20
DL21	130	39	DL18
DL19	131	40	DL16
VSS	132	41	VSS
DL17	133	42	DP6
CWE6	134	43	DL14
DL15	135	44	DL12
DL13	136	45	DL11
VSS	137	46	VSS
DL10	138	47	DL9
DL8	139	48	DP5
CWE5	140	49	DL7
DL6	141	50	DL4
VCC3	142	51	VCC3
DL5	143	52	DL3
DL2	144	53	DL1
VSS	145	54	DL0
CLK3	146	55	VSS
VSS	147	56	CLK2
CLK4	148	57	VSS
VSS	149	58	DP4
CWE4	150	59	COE0
ALE	151	60	COE1
VCC3	152	61	VCC3
ADDR1	153	62	ADDR0
RESERVED	154	63	RESERVED
CNTEN0	155	64	ADS0
CNTEN1	156	65	ADS1
VCC5	157	66	VCC5
VCC5	158	67	VCC5
A27	159	68	A28
A24	160	69	A26
A22	161	70	A25
A20	162	71	A23
VSS	163	72	VSS
A18	164	73	A21
A16	165	74	A19
A15	166	75	A17
A14	167	76	A13
VCC3	168	77	VCC3
A10	169	78	A12
A8	170	79	A11
A6	171	80	A9
VSS	172	81	VSS
A4	173	82	A7
A2	174	83	A5
A1	175	84	A3
BURSTMODE	176	85	A0
VCC5	177	86	VCC5
VALIDIN	178	87	TCLR
TWE	179	88	MATCH
STANDBY	180	89	TOE
DIRTYOUT	181	90	DIRTYIN
VSS	182	91	VSS

**NOTES:**

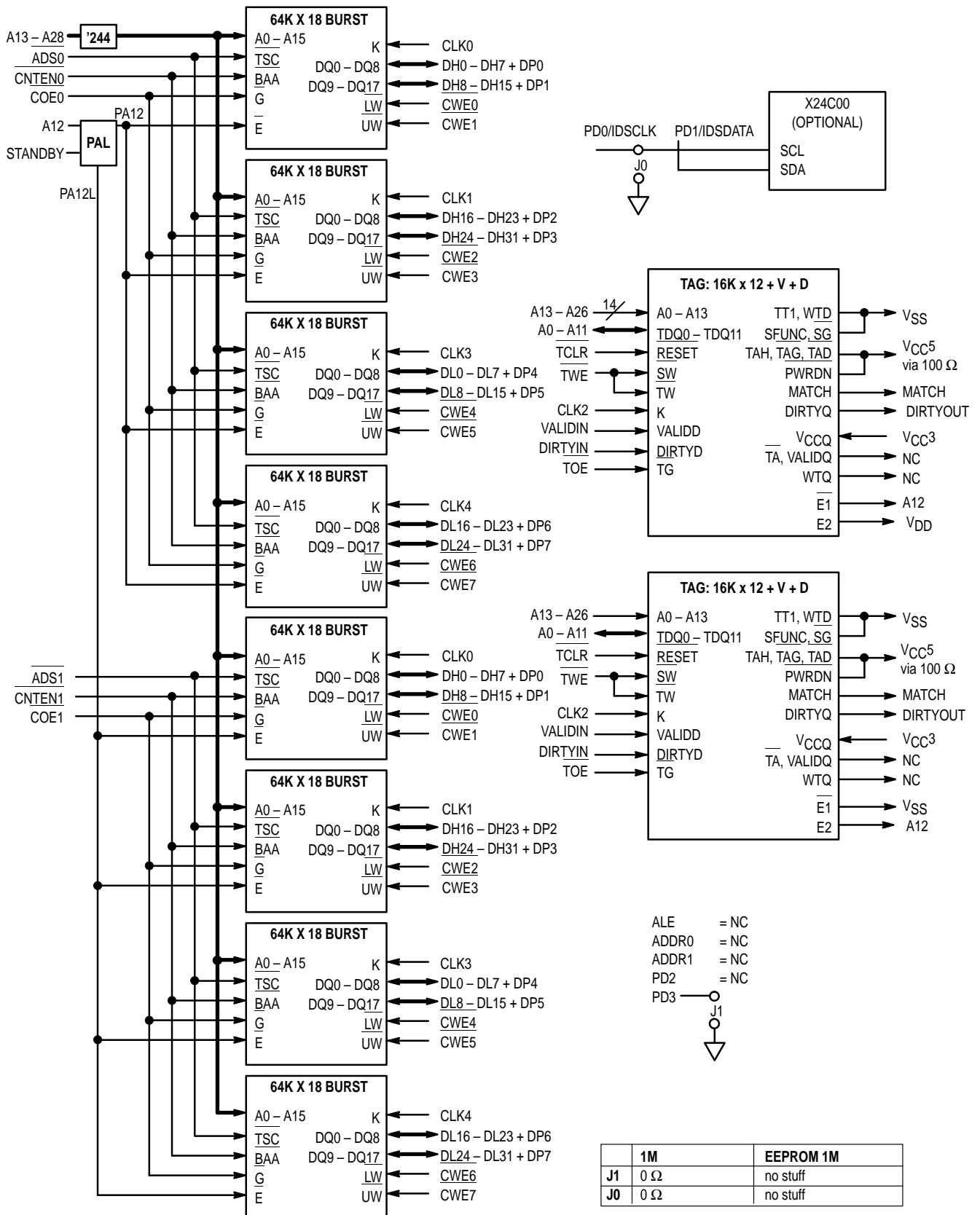
1. VCC5 and VCC3 must be connected on all modules.

## MPC2104/MPC2105 BLOCK DIAGRAM



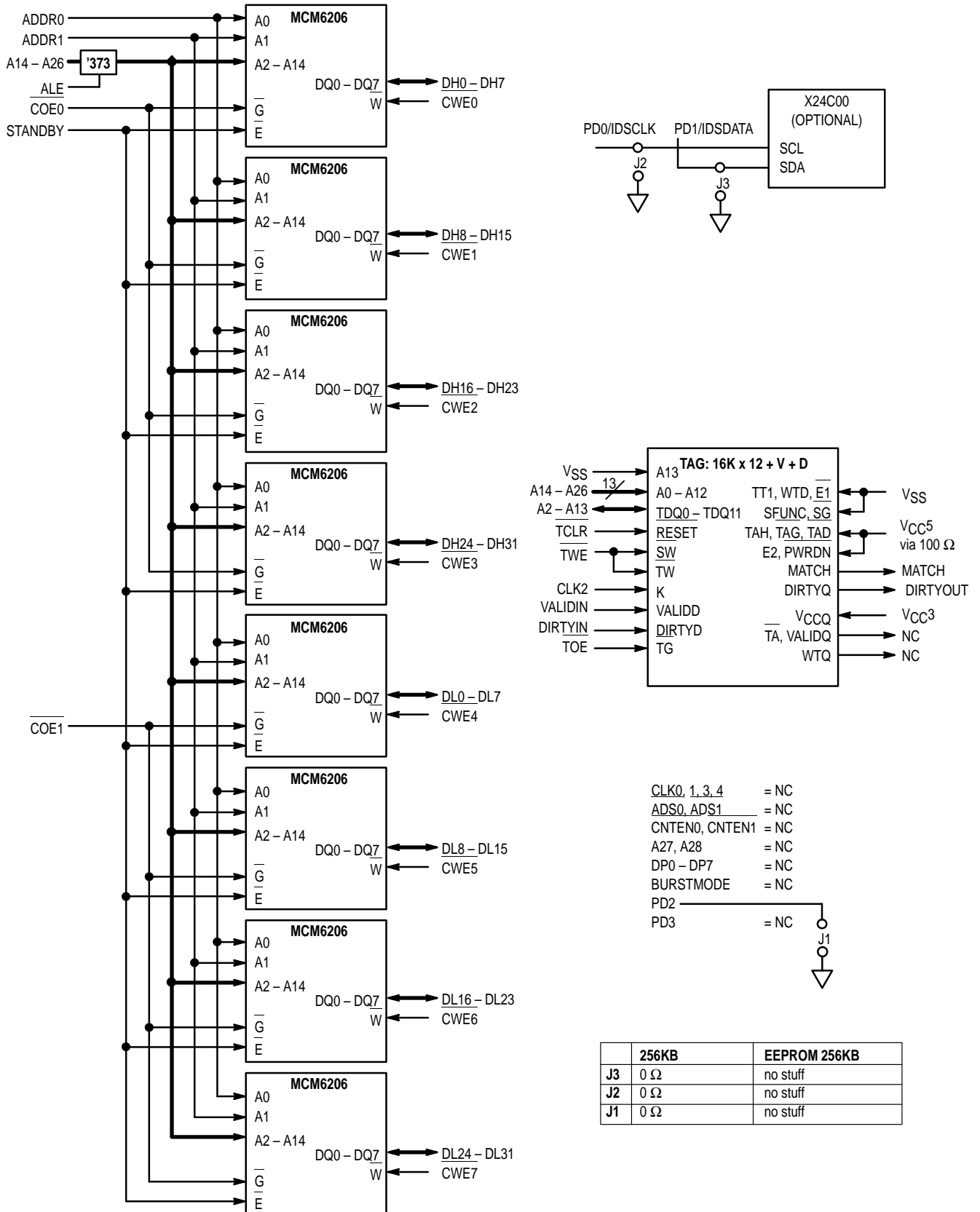
Note: MPC2104 utilizes 32K x 18 BurstRAMs. MPC2105 utilizes 64K x 18 BurstRAMs.

## MPC2106 BLOCK DIAGRAM



Note: All 64K X 18 TSP signals are tied to V<sub>CC</sub> via a 100 Ω resistor. Edge connector A28 connects to the 64K x 18 A0; edge connector A27 connects to the 64K x 18 A1.

## MPC2107 BLOCK DIAGRAM



	256KB	EEPROM 256KB
J3	0 Ω	no stuff
J2	0 Ω	no stuff
J1	0 Ω	no stuff

## PIN DESCRIPTIONS

Pin Locations	Symbol	Type	Description
68, 69, 70, 71, 73, 74, 75, 76, 78, 79, 80, 82, 83, 84, 85, 159, 160, 161, 162, 164, 165, 166, 167, 169, 170, 171, 173, 174, 175	A0 – A28	Input	Address Inputs – (MSB:0, LSB:28)
62	ADDR0	Input	Least significant address bit when asynchronous Data RAMs are used.
153	ADDR1	Input	Next to least significant address bit when asynchronous Data RAMs are used.
30, 56, 117, 146, 148	CLK0 – CLK4	Input	Clock Inputs – CLK2 is for Tag RAM, CLK0, 1, 3, and 4 are for Data RAMs only. For MPC2106 use all the clocks. For MPC2104 or MPC2105 use CLK0–CLK2 only. For MPC2107 use CLK2 only.
4, 5, 6, 7, 10, 11, 12, 14, 16, 17, 19, 20, 22, 24, 25, 26, 27, 95, 96, 97, 98, 101, 102, 103, 105, 107, 108, 110, 111, 113, 115, 119	DH0 – DH31	I/O	High Data Bus – (MSB:0, LSB:31)
32, 33, 34, 37, 38, 39, 40, 43, 44, 45, 47, 49, 50, 52, 53, 54, 121, 122, 124, 125, 126, 129, 130, 131, 133, 135, 136, 138, 139, 141, 143, 144	DL0 – DL31	I/O	Low Data Bus – (MSB:0, LSB:31)
9, 15, 21, 28, 35, 42, 48, 58	DP0 – DP7	I/O	Data Parity Bits – (MSB:0, LSB:7)
3, 94	PD2, PD3	Output	Presence detect bits.
2	PD0/IDSCCLK	Input	Presence detect bit 0/EEPROM serial clock. (EEPROM option only.)
93	PD1/IDSDATA	I/O	Presence detect bit 1/EEPROM serial data. (EEPROM option only.)
64, 65	ADS0, ADS1	Input	Data RAM Address Strobe – For MPC2104 or MPC2105 use ADS0 only. For MPC2106 use ADS0, ADS1.
151	ALE	Input	Data RAM Address Latch Enable – Use for asynchronous Data RAM only.
155, 156	CNTEN0, CNTEN1	Input	Data RAM Count Enables – For MPC2104 or MPC2105 use CNTEN0 only. For MPC2106 use CNTEN0, CNTEN1.
59, 60	COE0, COE1	Input	Data RAM Output Enables – For MPC2104 or MPC2105 use COE0 only. For all others use COE0, COE1.
100, 106, 112, 120, 128, 134, 140, 150	CWE0 – CWE7	Input	Data RAM Write Enables – (MSB:0, LSB:7)
87	TCLR	Input	Tag RAM clear.
88	MATCH	Output	Tag RAM active high match indication.
178	VALIDIN	Input	Tag RAM valid bit.
179	TWE	Input	Tag RAM write enable.
89	TOE	Input	Tag RAM output enable.
90	DIRTYIN	Input	Dirty input bit.
181	DIRTYOUT	Output	Dirty output bit.
180	STANDBY	Input	Standby pin. Reduces standby power consumption.
176, 63, 154	RESERVED		Reserved pin.
8, 23, 51, 61, 77, 99, 114, 142, 152, 168	V <sub>CC3</sub>	Input	+ 3.3 V power supply. Must be connected.
18, 36, 66, 67, 86, 109, 127, 157, 158, 177	V <sub>CC5</sub>	Input	+ 5 V power supply. Must be connected.
1, 13, 29, 31, 41, 46, 55, 57, 72, 81, 91, 92, 104, 116, 118, 123, 132, 137, 145, 147, 149, 163, 172, 182	V <sub>SS</sub>	Input	Ground
176	BURSTMODE	Input	Burstmode. 0 = Linear, 1 = Interleaved.

**DATA RAM MCM67M518, MCM67M618 SYNCHRONOUS TRUTH TABLE** (See Notes 1, 2, and 3)

STANDBY	ADS0	CNTEN0	CWEx	CLKx	Address Used	Operation
H	L	X	X	L–H	N/A	Deselected
L	L	X	L	L–H	External Address	Write Cycle, Begin Burst
L	L	X	H	L–H	External Address	Read Cycle, Begin Burst
X	H	L	L	L–H	Next Address	Write Cycle, Continue Burst
X	H	L	H	L–H	Next Address	Read Cycle, Continue Burst
X	H	H	L	L–H	Current Address	Write Cycle, Suspend Burst
X	H	H	H	L–H	Current Address	Read Cycle, Suspend Burst

NOTES:

1. X means Don't Care.
2. All inputs except COE must meet set-up and hold times for the low-to-high transition of clock (CLK0 – CLK4).
3. Wait states are inserted by suspending burst.

**ASYNCHRONOUS TRUTH TABLE** (See Notes 1 and 2)

Operation	COE	I/O Status
Read	L	Data Out (DQ0 – DQ8)
Read	H	High-Z
Write	X	High-Z — Data In
Deselected	X	High-Z

NOTES:

1. X means Don't Care.
2. For a write operation following a read operation, COE must be high before the input data required set-up time and held high through the input data hold time.

**DATA RAM MCM6206 ASYNCHRONOUS TRUTH TABLE** (See Notes 1 and 2)

STANDBY	COE0, COE1	CWE0 – CWE7	Operation	I/O Status
H	X	X	Deselected	High-Z
L	H	H	Output Disabled	High-Z
L	L	H	Read	Data Out
L	X	L	Write	High-Z

NOTES:

1. X means Don't Care.
2. For a write operation following a read operation, COE0, and COE1 must be high before the input data required set-up time, and held high through the input data hold time.

**ABSOLUTE MAXIMUM RATINGS** (Voltages Referenced to  $V_{SS} = 0$  V)

Rating	Symbol	Value	Unit
Power Supply Voltage	$V_{CC}$	- 0.5 to + 7.0	V
Voltage Relative to $V_{SS}$	$V_{in}, V_{out}$	- 0.5 to $V_{CC} + 0.5$	V
Output Current (per I/O)	Data RAM Tag $I_{out}$	$\pm 30$ $\pm 20$	mA
Power Dissipation	$P_D$	8.1	W
Temperature Under Bias	$T_{bias}$	- 10 to + 85	°C
Operating Temperature	$T_A$	0 to +70	°C
Storage Temperature	$T_{stg}$	- 55 to + 125	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

This BiCMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established.

This device contains circuitry that will ensure the output devices are in High-Z at power up.

## DC OPERATING CONDITIONS AND CHARACTERISTICS

( $V_{CC} = 5.0\text{ V} \pm 5\%$ ,  $T_A = 0$  to  $+70^\circ\text{C}$ , Unless Otherwise Noted)

### RECOMMENDED OPERATING CONDITIONS (Voltages referenced to $V_{SS} = 0\text{ V}$ )

Parameter	Symbol	Min	Max	Unit
Supply Voltage (Operating Voltage Range)	$V_{CC}$	4.75	5.25	V
Input High Voltage	$V_{IH}$	2.2	$V_{CC} + 0.3^{**}$	V
Input Low Voltage	$V_{IL}$	$-0.5^*$	0.8	V

\*  $V_{IL}$  (min) =  $-0.5\text{ V}$  dc;  $V_{IL}$  (min) =  $-2.0\text{ V}$  ac (pulse width  $\leq 20\text{ ns}$ ) for  $I \leq 20.0\text{ mA}$ .

\*\*  $V_{IH}$  (max) =  $V_{CC} + 0.3\text{ V}$  dc;  $V_{IH}$  (max) =  $V_{CC} + 2.0\text{ V}$  ac (pulse width  $\leq 20\text{ ns}$ ) for  $I \leq 20.0\text{ mA}$ .

### DC CHARACTERISTICS

Parameter	Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, $V_{in} = 0$ to $V_{CC}$ )	Data RAM Tag $I_{lkg}(I)$	—	$\pm 1.0$ $\pm 5.0$	$\mu\text{A}$
Output Leakage Current ( $COE = V_{IH}$ , $V_{out} = 0$ to $V_{CC}$ )	Data RAM Tag $I_{lkg}(O)$	—	$\pm 1.0$ $\pm 5.0$	$\mu\text{A}$
TTL Output Low Voltage ( $I_{OL} = +8.0\text{ mA}$ )	$V_{OL}$	—	0.4	V
TTL Output High Voltage ( $I_{OH} = -4.0\text{ mA}$ )	$V_{OH}$	2.4	—	V

### POWER SUPPLY CURRENTS

Parameter	Symbol	Max	Unit
AC Supply Current ( $COE = V_{IH}$ , $E = V_{IL}$ , $I_{out} = 0\text{ mA}$ , All Inputs = $V_{IL}$ and $V_{IH}$ , $V_{IL} = 0.0\text{ V}$ and $V_{IH} \geq 3.0\text{ V}$ , Cycle Time $\geq 20\text{ ns}$ )	MPC2104 MPC2105 MPC2106 MPC2107 $I_{CCA}$	1480 1420 2840 1400	mA
AC Standby Current ( $E = V_{IH}$ , $I_{out} = 0\text{ mA}$ , All Inputs = $V_{IL}$ or $V_{IH}$ , $V_{IL} = 0.0\text{ V}$ and $V_{IH} \geq 3.0\text{ V}$ , Cycle Time $\geq 20\text{ ns}$ )	MPC2104 MPC2105 MPC2106 MPC2107 $I_{SB1}$	620 700 1400 960	mA

### CAPACITANCE ( $f = 1.0\text{ MHz}$ , $dV = 3.0\text{ V}$ , $T_A = 25^\circ\text{C}$ , Periodically Sampled Rather Than 100% Tested)

Parameter	Symbol	Typ	Max	Unit
Input Capacitance (A13 – A28) (Data RAM Control Pins) (CLK0 – CLK4) (Tag Control Pins)	$C_{in}$	— 16 8 —	15 20 10 5	pF
Tag Output Capacitance (MATCH, DIRTYOUT)	$C_{out}$	—	7	pF
Data RAM Input/Output Capacitance (DH0 – DH31, DL0 – DL31)	$C_{I/O}$	6	8	pF
Tag Input/Output Capacitance (A0 – A11)	$C_{I/O}$	—	7	pF



## DATA RAMs AC OPERATING CONDITIONS AND CHARACTERISTICS

(V<sub>CC</sub> = 5.0 V ± 5% T<sub>A</sub> = 0 to + 70°C, Unless Otherwise Noted)

Input Timing Measurement Reference Level ..... 1.5 V  
 Input Pulse Levels ..... 0 to 3.0 V  
 Input Rise/Fall Time ..... 3 ns

Output Timing Reference Level ..... 1.5 V  
 Output Load ..... See Figure 1A Unless Otherwise Noted

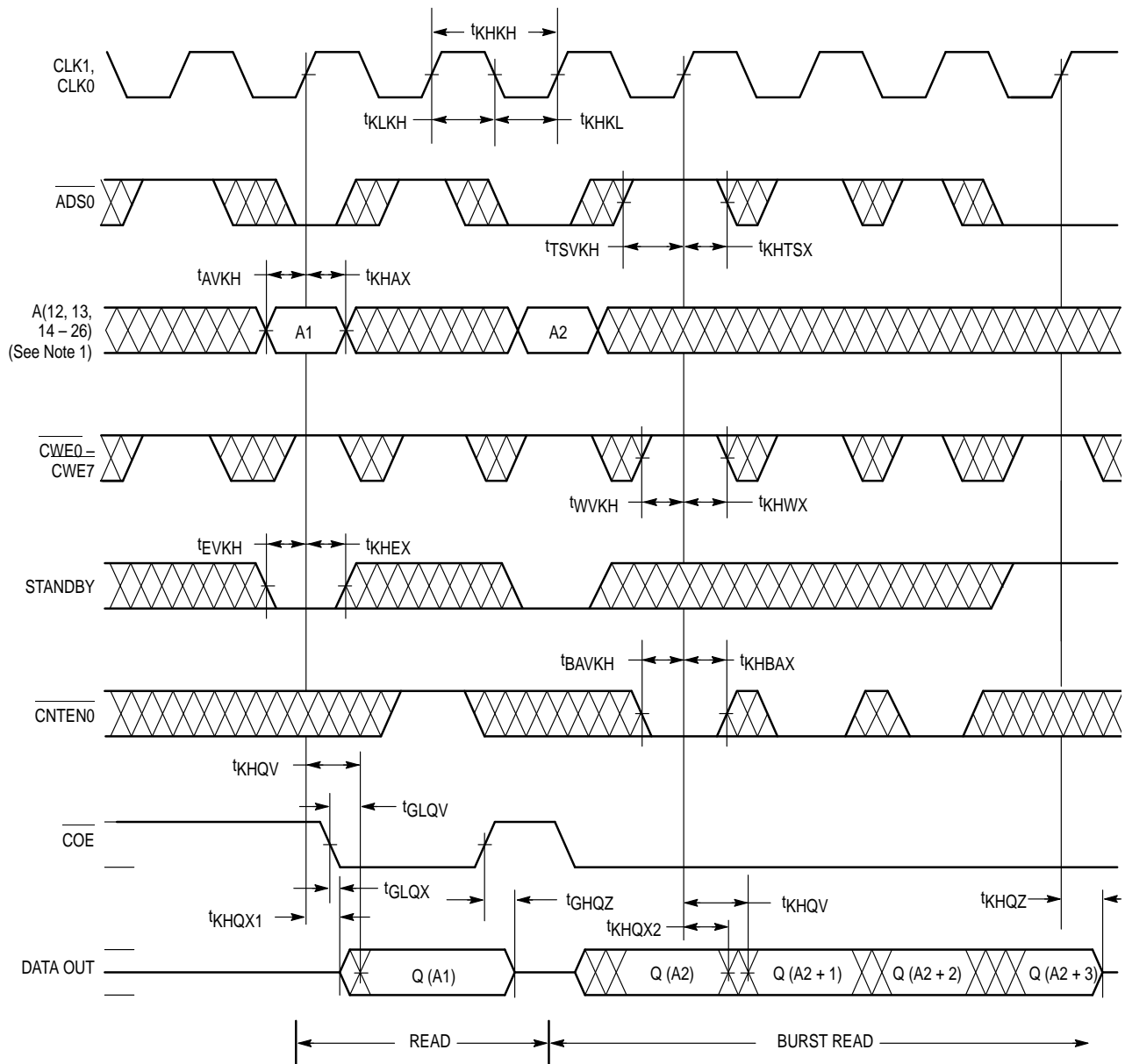
### SYNCHRONOUS DATA RAMs READ/WRITE CYCLE TIMING (See Notes 1, 2, 3, and 7)

Parameter	Symbol	MPC2104 MPC2105 MPC2106		Unit	Notes	
		Min	Max			
Cycle Time	t <sub>KHKH</sub>	15	—	ns		
Clock Access Time	t <sub>KHQV</sub>	—	9	ns	4	
Output Enable to Output Valid	t <sub>GLQV</sub>	—	5	ns		
Clock High to Output Active	t <sub>KHQX1</sub>	6	—	ns		
Clock High to Output Change	t <sub>KHQX2</sub>	3	—	ns		
Output Enable to Output Active	t <sub>GLQX</sub>	0	—	ns		
Output Disable to Q High-Z	t <sub>GHQZ</sub>	2	6	ns		
Clock High to Q High-Z	t <sub>KHQZ</sub>	—	6	ns		
Clock High Pulse Width	t <sub>KHKL</sub>	5	—	ns		
Clock Low Pulse Width	t <sub>KLKH</sub>	5	—	ns		
Setup Time	Address t <sub>AVKH</sub>	7.5	—	ns	5, 6	
Setup Times:	Address Status Data In Write Address Advance Chip Enable	t <sub>SVKH</sub> t <sub>DVKH</sub> t <sub>WVKH</sub> t <sub>BAVVKH</sub> t <sub>EVKH</sub>	2.5	—	ns	5
Hold Times:	Address Address Status Data In Write Address Advance Chip Enable	t <sub>KHAX</sub> t <sub>KHTSX</sub> t <sub>KHDX</sub> t <sub>KHDX</sub> t <sub>KHBAX</sub> t <sub>KHEX</sub>	0.5	—	ns	5

**NOTES:**

1. In setup and hold times, W (write) refers to either one or both byte write enables LW and UW.
2. All read and write cycle timings are referenced from CLK or COE.
3. COE is a don't care when UW or LW is sampled low.
4. Maximum access times are guaranteed for all possible PowerPC external bus cycles.
5. This is a synchronous device. All addresses must meet the specified setup and hold times for **ALL** rising edges of CLK whenever TSP or TSC is low, and the chip is selected. All other synchronous inputs must meet the specified setup and hold times for **ALL** rising edges of CLK when the chip is enabled. Chip enable must be valid at each rising edge of clock for the device (when TSP or TSC is low) to remain enabled.
6. 5 ns of set-up delay is incurred in address buffers.
7. Applies to MPC2104, MPC2105, and MPC2106.

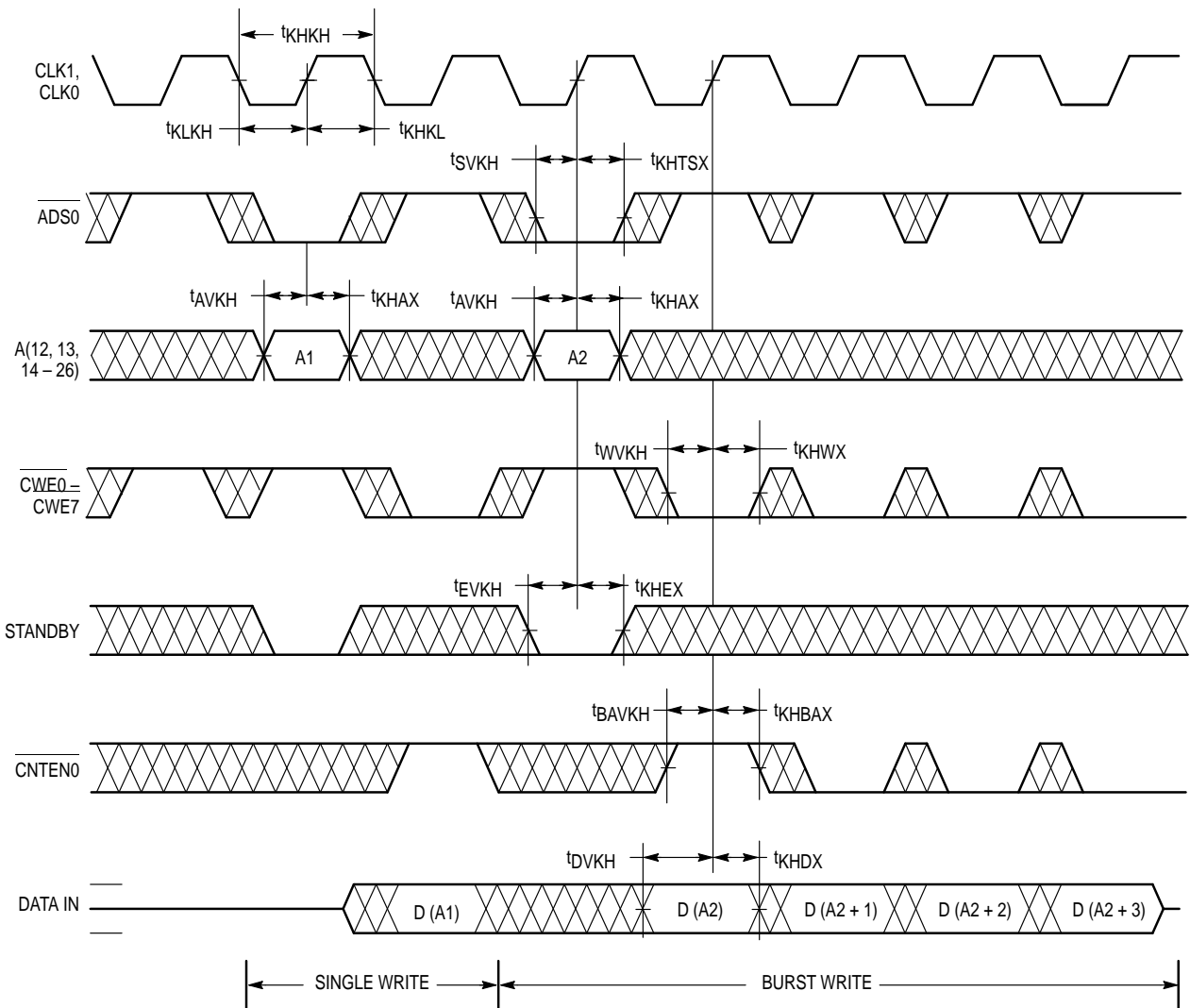
### SYNCHRONOUS DATA RAM READ CYCLE



**NOTES:**

1. Cache addresses used are: 14 – 26 for MPC2104 and MPC2107; 13 – 26 for MPC2105; and 12 – 26 for MPC2106.
2. Q1 (A2) represents the first output from the external address A2; Q2 (A2) represents the next output data in the burst sequence with A2 as the base address.

## SYNCHRONOUS DATA RAM WRITE CYCLE



**NOTES:**

1. Cache addresses used are: 14 – 26 for MPC2104 and MPC2107; 13 – 26 for MPC2105; and 12 – 26 for MPC2106.
2.  $COE0 = V_{IH}$

## AC OPERATING CONDITIONS AND CHARACTERISTICS

( $V_{CC} = 5.0\text{ V} \pm 5\%$   $T_A = 0$  to  $+70^\circ\text{C}$ , Unless Otherwise Noted)

Input Timing Measurement Reference Level ..... 1.5 V	Output Timing Reference Level ..... 1.5 V
Input Pulse Levels ..... 0 to 3.0 V	Output Load ..... See Figure 1A Unless Otherwise Noted
Input Rise/Fall Time ..... 3 ns	

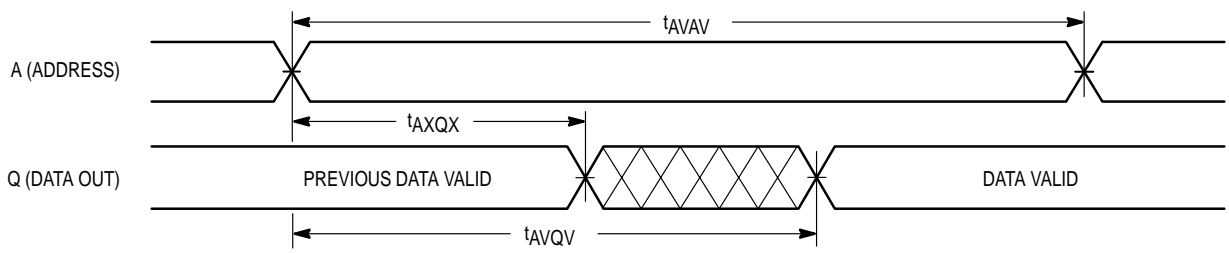
### ASYNCHRONOUS DATA RAMs READ CYCLE TIMING (See Notes 1 and 8)

Parameter	Symbol	MPC2107–15		Unit	Notes
		Min	Max		
Cycle Time	$t_{AVAV}$	15	—	ns	2
Address Access Time	$t_{AVQV}$	—	15	ns	
Enable Access Time	$t_{ELQV}$	—	15	ns	3
Output Enable Access Time	$t_{GLQV}$	—	8	ns	
Output Hold from Address Change	$t_{AXQX}$	4	—	ns	4, 5, 6
Enable Low to Output Active	$t_{ELQX}$	4	—	ns	4, 5, 6
Enable High to Output High–Z	$t_{EHQZ}$	0	8	ns	4, 5, 6
Output Enable Low to Output Active	$t_{GLQX}$	0	—	ns	4, 5, 6
Output Enable High to Output High–Z	$t_{GHQZ}$	0	7	ns	4, 5, 6
Power Up Time	$t_{ELICCH}$	0	—	ns	
Power Down Time	$t_{EHICCL}$	—	15	ns	

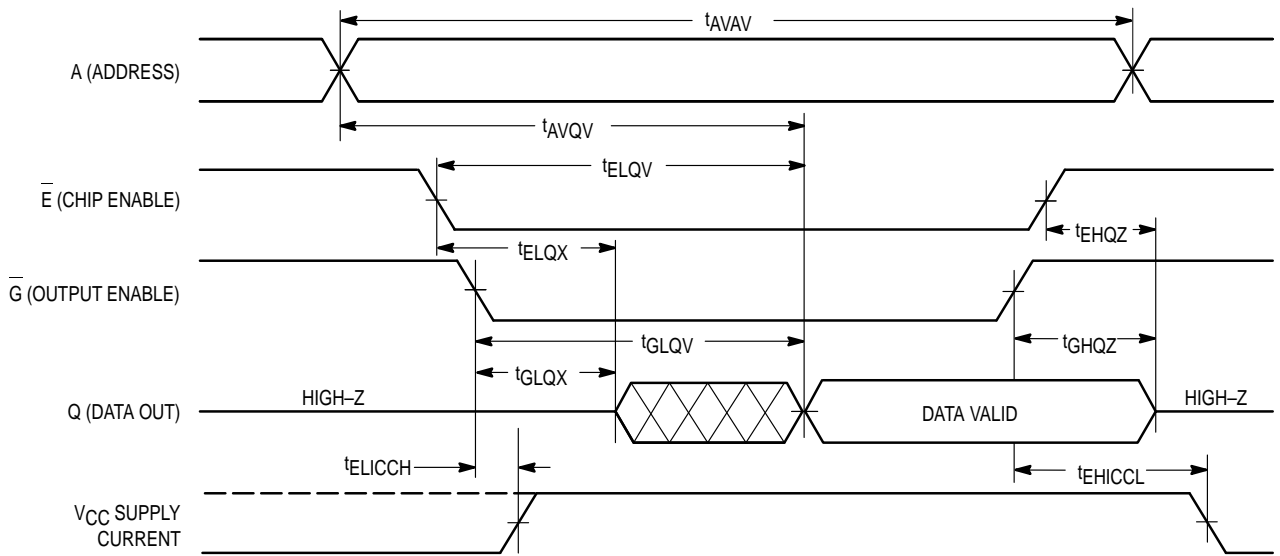
#### NOTES:

1. W is high for read cycle.
2. All timings are referenced from the last valid address to the first transitioning address.
3. Addresses valid prior to or coincident with E going low.
4. At any given voltage and temperature,  $t_{EHQZ}(\text{max})$  is less than  $t_{ELQX}(\text{min})$ , and  $t_{GHQZ}(\text{max})$  is less than  $t_{GLQX}(\text{min})$ , both for a given device and from device to device.
5. Transition is measured  $\pm 500$  mV from steady-state voltage with load of Figure 1B.
6. This parameter is sampled and not 100% tested.
7. Device is continuously selected ( $E = V_{IL}$ ,  $COE0 = V_{IL}$ ).
8. Applies to MPC2107.

**ASYNCHRONOUS READ CYCLE 1 (See Note 7)**



**ASYNCHRONOUS READ CYCLE 2 (See Note 3)**



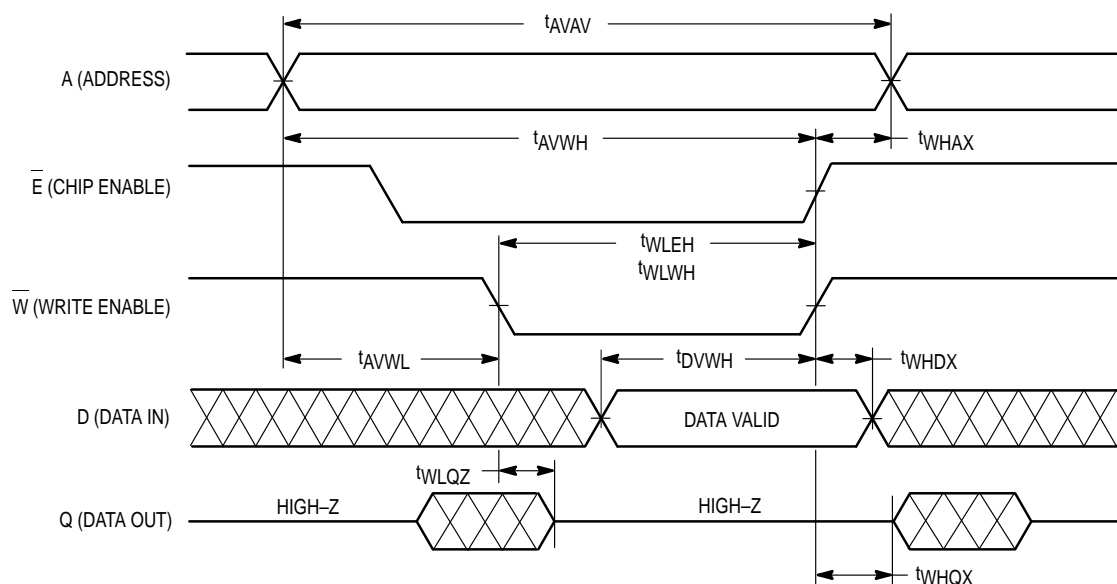
**ASYNCHRONOUS DATA RAMs WRITE CYCLE 1** (See Notes 1 and 2)

Parameter	Symbol	MPC2107-15		Unit	Notes
		Min	Max		
Write Cycle Time	$t_{AVAV}$	15	—	ns	3
Address Set-up Time	$t_{AVWL}$	0	—	ns	
Address Valid to End of Write	$t_{AVWH}$	12	—	ns	
Write Pulse Width	$t_{WLWH}$ $t_{WLEH}$	12	—	ns	
Write Pulse Width, G High	$t_{WLWH}$ $t_{WLEH}$	10	—	ns	4
Data Valid to End of Write	$t_{DVWH}$	7	—	ns	
Data Hold Time	$t_{WHDX}$	0	—	ns	
Write Low to Output High-Z	$t_{WLQZ}$	0	7	ns	5,6,7
Write High to Output Active	$t_{WHQX}$	5	—	ns	5,6,7
Write Recovery Time	$t_{WHAX}$	0	—	ns	

**NOTES:**

1. A write occurs during the overlap of  $\bar{E}$  low and  $\bar{W}$  low.
2. If  $\bar{E}$  goes low coincident with or after  $\bar{W}$  goes low, the output will remain in a high impedance state.
3. All timings are referenced from the last valid address to the first transitioning address.
4. If  $E \geq V_{IH}$ , the output will remain in a high impedance state.
5. At any given voltage and temperature,  $t_{WLQZ}$  (max) is less than  $t_{WHQX}$  (min), both for a given device and from device to device.
6. Transition is measured  $\pm 500$  mV from steady-state voltage with load of Figure 1B.
7. This parameter is sampled and not 100% tested.

**ASYNCHRONOUS WRITE CYCLE 1 ( $\bar{W}$  Controlled, See Notes 1 and 2)**



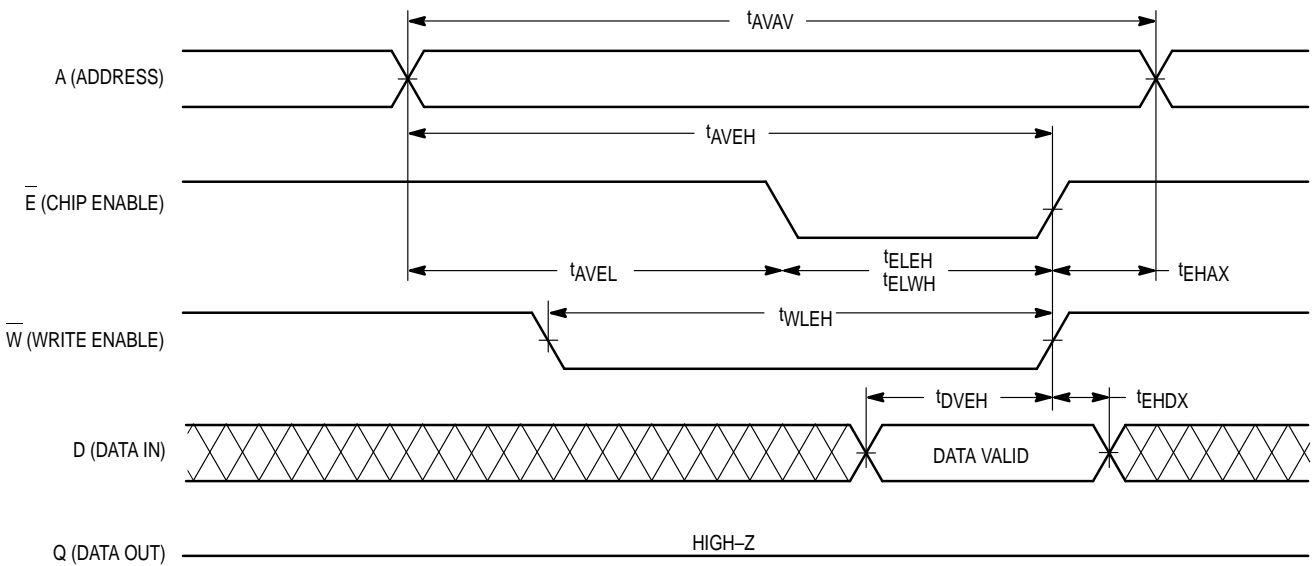
**ASYNCHRONOUS DATA RAMs WRITE CYCLE 2 ( $\bar{E}$  Controlled, See Notes 1 and 2)**

Parameter	Symbol	MPC2107-15		Unit	Notes
		Min	Max		
Write Cycle Time	$t_{AVAV}$	15	—	ns	0
Address Setup Time	$t_{AVEL}$	0	—	ns	
Address Valid to End of Write	$t_{AVEH}$	12	—	ns	
Enable to End of Write	$t_{ELEH}$ $t_{ELWH}$	10	—	ns	3, 4
Data Valid to End of Write	$t_{DVEH}$	7	—	ns	
Data Hold Time	$t_{EHDX}$	0	—	ns	
Write Recovery Time	$t_{EHAX}$	0	—	ns	

NOTES:

1. A write occurs during the overlap of  $\bar{E}$  low and  $\bar{W}$  low.
2. All timings are referenced from the last valid address to the first transitioning address.
3. If  $\bar{E}$  goes low coincident with or after  $\bar{W}$  goes low, the output will remain in a high impedance state.
4. If  $\bar{E}$  goes high coincident with or before  $\bar{W}$  goes high, the output will remain in a high impedance state.

**ASYNCHRONOUS WRITE CYCLE 2 ( $\bar{E}$  Controlled, See Note 1)**



## TAG RAM

**RESET FUNCTION TRUTH TABLE** (See Notes 1 and 2)

TCLR	CLK	TWE	TAG	VLD <sub>out</sub>	DTY <sub>out</sub>	WT <sub>out</sub>	MATCH	TA	Operation	POWER
L	L-H	H	High-Z	L <sup>(3)</sup>	L <sup>(3)</sup>	L <sup>(3)</sup>	L <sup>(3)</sup>	High-Z	Reset Status	Active
L	L-H	L	—	—	—	—	—	—	Not Allowed	—

NOTES:

1. H = V<sub>IH</sub>, L = V<sub>IL</sub>, X = don't care, — = unrelated.
2. TOE is X for this table.

**READ FUNCTION TRUTH TABLE** (See Notes 1, 2, and 3)

TOE	TWE	CLK	TAG	VLD <sub>in</sub>	DTY <sub>in</sub>	WT <sub>in</sub>	VLD <sub>out</sub>	DTY <sub>out</sub>	WT <sub>out</sub>	MATCH	Operation
L	H	X	D <sub>OUT</sub>	—	—	—	—	—	—	D <sub>OUT</sub>	Read Tag I/O
H	X	X	High-Z	—	—	—	—	—	—	—	Tag I/O Disable

**WRITE FUNCTION TRUTH TABLE** (See Notes 1 and 2)

TOE	TWE	CLK	TAG	VLD <sub>in</sub>	DTY <sub>in</sub>	WT <sub>in</sub>	VLD <sub>out</sub>	DTY <sub>out</sub>	WT <sub>out</sub>	MATCH	Operation
H	L	L-H	D <sub>IN</sub>	—	—	—	D <sub>OUT</sub>	D <sub>OUT</sub>	D <sub>OUT</sub>	L	Write Tag I/O
L	L	L-H	—	—	—	—	—	—	—	—	Not Allowed

NOTES:

1. H = V<sub>IH</sub>, L = V<sub>IL</sub>, X = don't care, — = unrelated.
2. This table applies when RESET and PWRDN are high.
3. D<sub>OUT</sub> in this case is the same as D<sub>IN</sub>. The input data is written through to the outputs during the write operation.

**MATCH FUNCTION TRUTH TABLE** (See Notes 1 through 4)

TOE	TWE	TAG	VLD <sup>(4)</sup>	DTY <sup>(4)</sup>	WT <sup>(4)</sup>	MATCH	Operation
X	X	—	—	—	—	D <sub>OUT</sub>	Selected
L	H	D <sub>OUT</sub>	—	—	—	L	Read Tag I/O
H	L	D <sub>IN</sub>	D <sub>IN</sub>	D <sub>IN</sub>	D <sub>IN</sub>	L	Write Tag I/O, Status Bits
H	H	TAG <sub>IN</sub>	L	—	—	L	Invalid Data – Dedicated Status Bits
H	H	TAG <sub>IN</sub>	H	—	—	M	Match – Dedicated Status Bits

NOTES:

1. H = V<sub>IH</sub>, L = V<sub>IL</sub>, X = don't care, — = unrelated.
2. M = high if TAG<sub>IN</sub> equals the memory contents at the address; M = low if TAG<sub>IN</sub> does not equal the contents at that address.
3. PWRDN and RESET are high for this table. OES and CLK are X.
4. This column represents the stored memory cell data for the given status bit at the selected address.



## TAG RAM AC OPERATING CONDITIONS AND CHARACTERISTICS

( $V_{CC} = 5.0\text{ V} \pm 5\%$ ,  $T_A = 0\text{ to } +70^\circ\text{C}$ , Unless Otherwise Noted)

Input Timing Measurement Reference Level ..... 1.5 V  
 Input Pulse Levels ..... 0 to 3.0 V  
 Input Rise/Fall Time ..... 3 ns

Output Timing Measurement Reference Level ..... 1.5 V  
 Output Load ..... Figure 1A Unless Otherwise Noted

### TAG RAM READ CYCLE (See Notes 1 through 4)

Parameter	Symbol	Tag RAM		Unit	Notes
		Min	Max		
Clock Access Time	$t_{KHQV}$	—	10	ns	
Output Enable to Output Valid	$t_{GLQV}$	—	8	ns	
Output Enable to Output Active	$t_{GLQX}$	0	—	ns	
Output Disable to Q High-Z	$t_{GHQZ}$	1	6	ns	
Status Bit Hold from Address Change	$t_{AXSX}$	3	—	ns	
Address Access Time Status Bits	$t_{AVSV}$	—	10	ns	
Tag Bit Hold from Address Change	$t_{AVQX}$	3	—	ns	
Address Access Time Tag Bits	$t_{AVQV}$	—	12	ns	

**NOTES:**

1. Set-up and hold times, W (write) refers to TWE.
2. A read cycle is defined by TWE high. A write cycle is defined by TWE low.
3. Maximum access times are guaranteed for all possible MC68040 and PowerPC external bus cycles.
4. Tag reads are asynchronous.

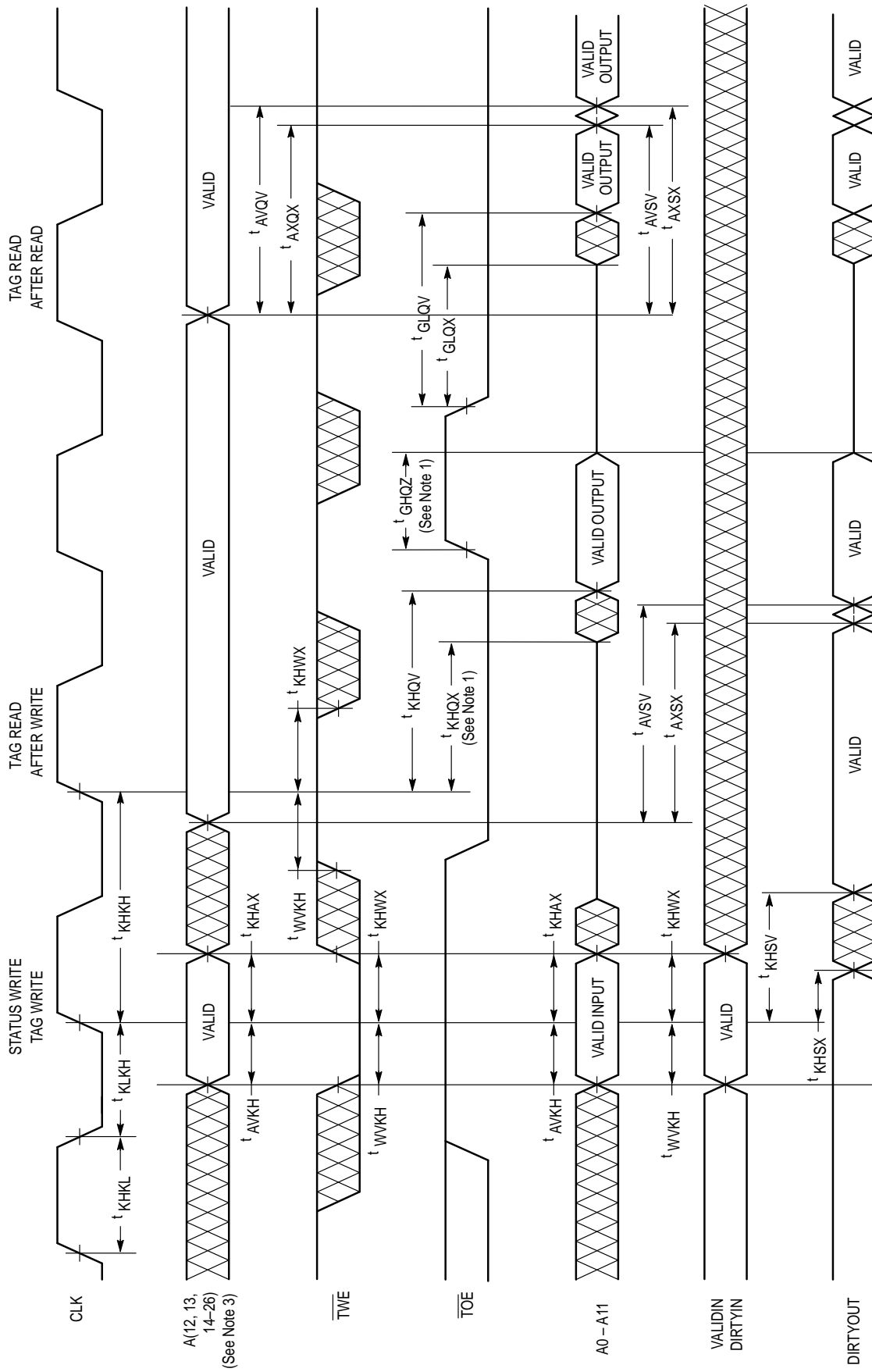
### TAG RAM WRITE CYCLE (See Notes 1 through 4)

Parameter	Symbol	Tag RAM		Unit	Notes
		Min	Max		
Cycle Time	$t_{KHKH}$	15	—	ns	
Clock High Pulse Width	$t_{KHKL}$	4.5	—	ns	
Clock Low Pulse Width	$t_{KLKH}$	4.5	—	ns	
Clock High to Output Active	$t_{KHQX}$	1.5	—	ns	
Set-up Times	Address Write	$t_{AVKH}$ $t_{WVKH}$	3	—	ns
Hold Times	Address Write	$t_{KHAX}$ $t_{KH WX}$	1.5	—	ns
Status Output Hold		$t_{KHSX}$	0	—	ns
Clock High to Status Bits Valid		$t_{KHSV}$	—	9	ns

**NOTES:**

1. Set-up and hold times, W (write) refers to TWE.
2. A read cycle is defined by TWE high. A write cycle is defined by TWE low.
3. Maximum access times are guaranteed for all possible MC68040 and PowerPC external bus cycles.
4. Tag writes are synchronous.

**TAG RAM WRITE AND READ CYCLES (See Note 2)**



NOTE:

1. Transition is measured plus or minus 200 mV from steady state.
2.  $\overline{TCLR}$  = High.
3. Cache addresses used are: 14-26 for MPC2004 and MPC2007; 13-26 for MPC2005; 12-26 for MPC2006 and MPC2009.

### TAG RAM MATCH CYCLE

Parameter	Symbol	Tag RAM		Unit	Notes
		Min	Max		
Clock High Write to MATCH Invalid	t <sub>KHML</sub>	—	7	ns	
Clock High Read to MATCH Valid	t <sub>KHMV</sub>	—	10	ns	
Address Valid to MATCH Valid	t <sub>AVMV</sub>	—	10	ns	
MATCH Valid Hold from Address Change	t <sub>AXMX</sub>	2	—	ns	
TOE Low to MATCH Invalid	t <sub>GLML</sub>	—	7	ns	
TOE High to MATCH Valid	t <sub>GHMX</sub>	—	8	ns	

### TAG RAM RESET (TCLR) CYCLE

Parameter	Symbol	Tag RAM		Unit	Notes
		Min	Max		
TCLR Set-up Time	t <sub>STC</sub>	4	—	ns	
TCLR Hold Time	t <sub>HTC</sub>	1	—	ns	
Status Bit Reset Time	t <sub>SRST</sub>	—	60	ns	
Status Bit Hold from TCLR Low	t <sub>SHRS</sub>	2	—	ns	
TCLR Low to MATCH Invalid	t <sub>RSML</sub>	—	10	ns	
TCLR High to MATCH Valid	t <sub>RSMV</sub>	—	100	ns	
TCLR Low to TAG High-Z	t <sub>RSQZ</sub>	—	10	ns	
TCLR High to TAG Active	t <sub>RSQX</sub>	—	100	ns	
STANDBY Set-up to TCLR Low	t <sub>PDSR</sub>	30	—	ns	
TCLR High to TWE Low	t <sub>RHWX</sub>	80	—	ns	

### AC TEST LOADS

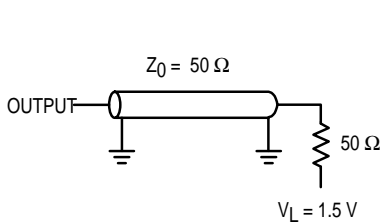


Figure 1A

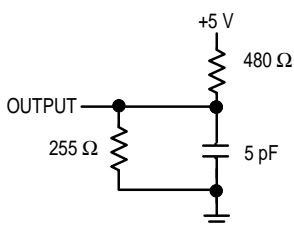
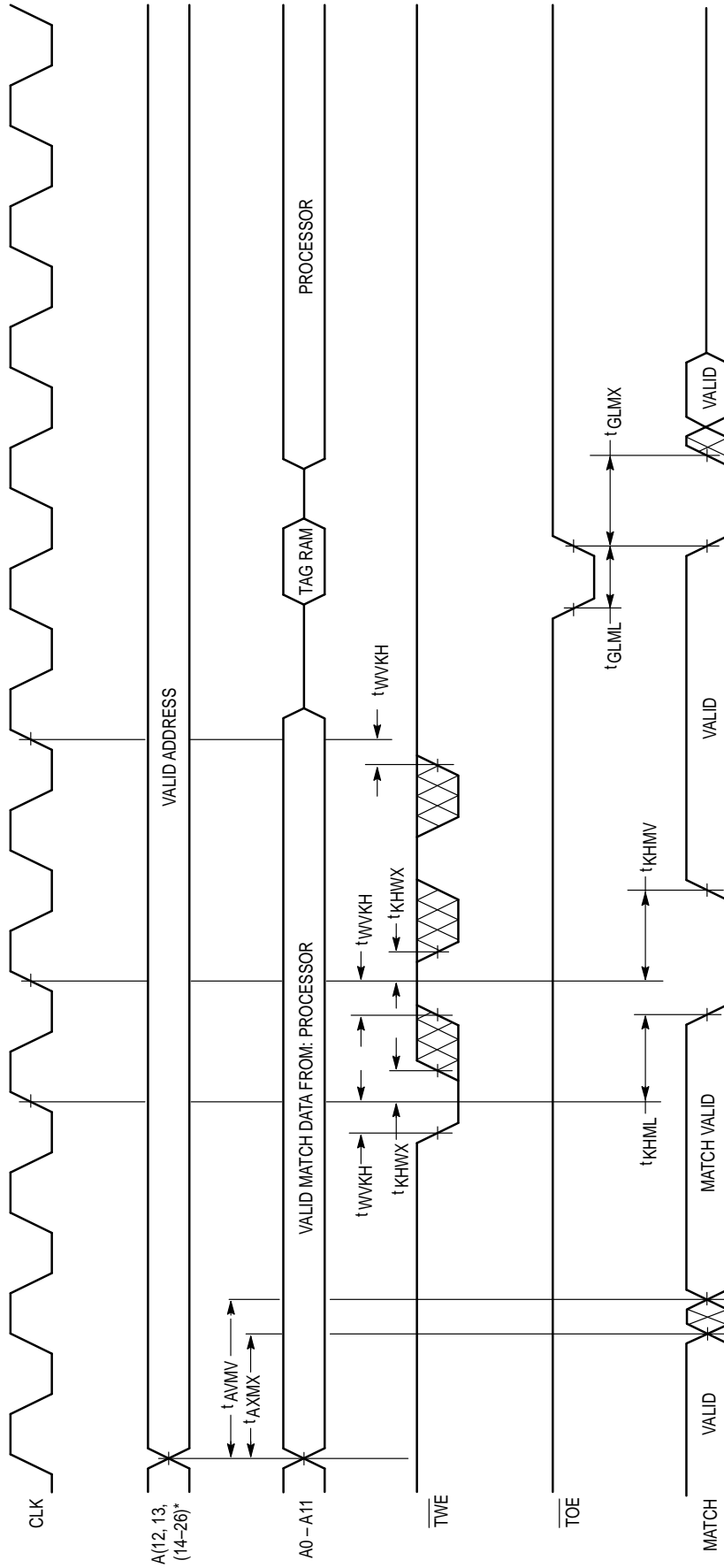


Figure 1B

### TIMING LIMITS

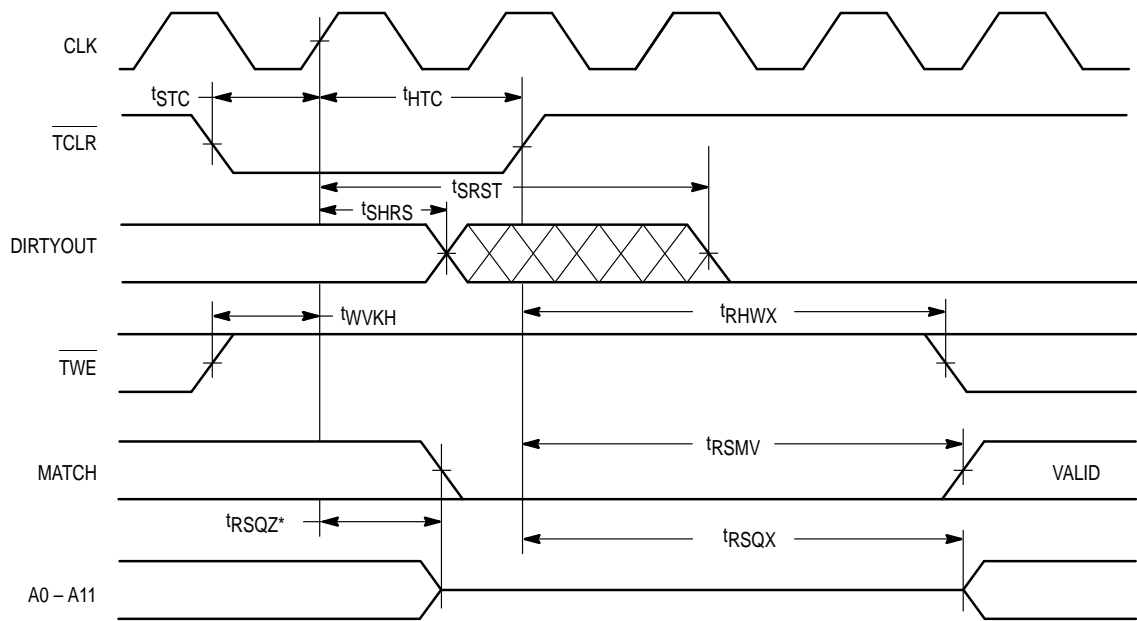
The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time (even though most devices do not require it). On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

### TAG RAM MATCH CYCLE



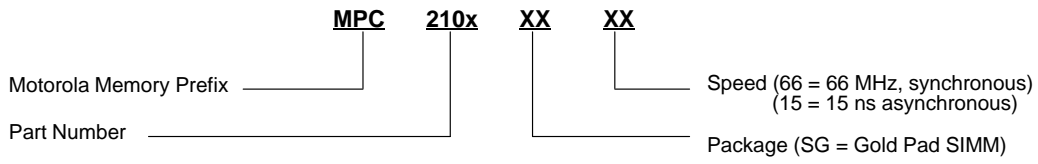
\* Cache addresses used are: 14-26 for MPC2004 and MPC2007; 13-26 for MPC2005; 12-26 for MPC2006.

### TAG RAM TCLR FUNCTION




\* Transition is measured plus or minus 200 mV from steady state.

**ORDERING INFORMATION**  
(Order by Full Part Number)



Full Part Numbers — MPC2104SG66  
MPC2105SG66  
MPC2106SG66  
MPC2107SG15

MPC2104 = 256KB, synchronous  
MPC2105 = 512KB, synchronous  
MPC2106 = 1MB, synchronous  
MPC2107 = 256KB, asynchronous

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